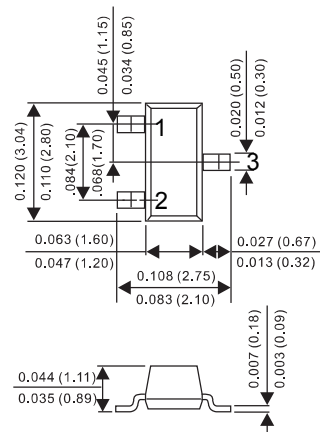


**Features**

- Fast Switching Speed
- For General Purpose Switching Applications
- High Conductance

SOT - 23

BAW56	BAV70	BAV99
MARKING:A1	MARKING:A4	MARKING:A7



Dimensions in inches and (millimeters)

Maximum ratings (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Limit	Unit
Reverse Voltage	V_R	70	V
Forward Current	I_F	200	mA
Non-Repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	2.0	A
Power Dissipation	P_D	225	mW
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	556	$^{\circ}\text{C/W}$
Junction Temperature	T_J	150	$^{\circ}\text{C}$
Storage Temperature range	T_{STG}	-55~+150	$^{\circ}\text{C}$

Electrical characteristics (AT $T_A=25^{\circ}\text{C}$ unless otherwise noted)

Off characteristics

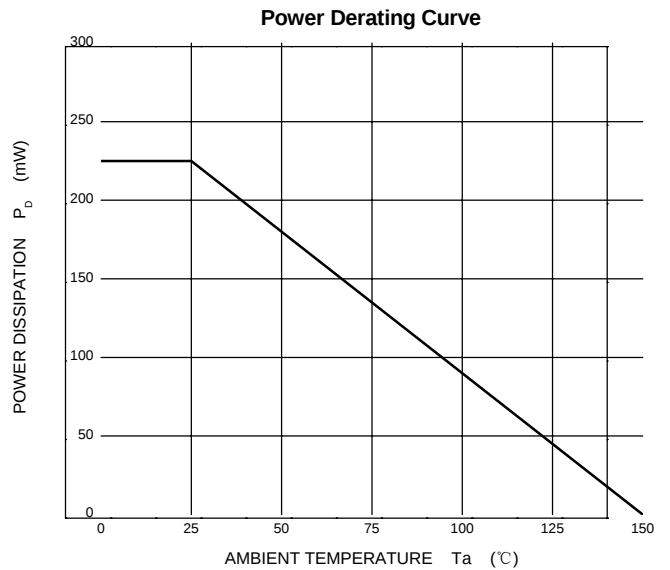
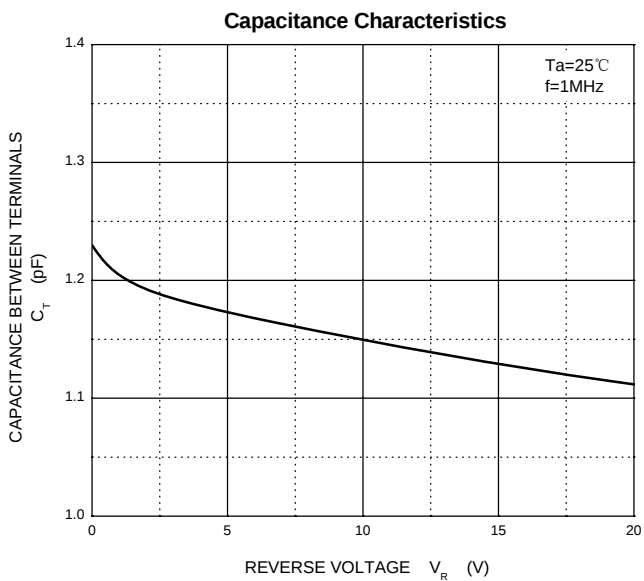
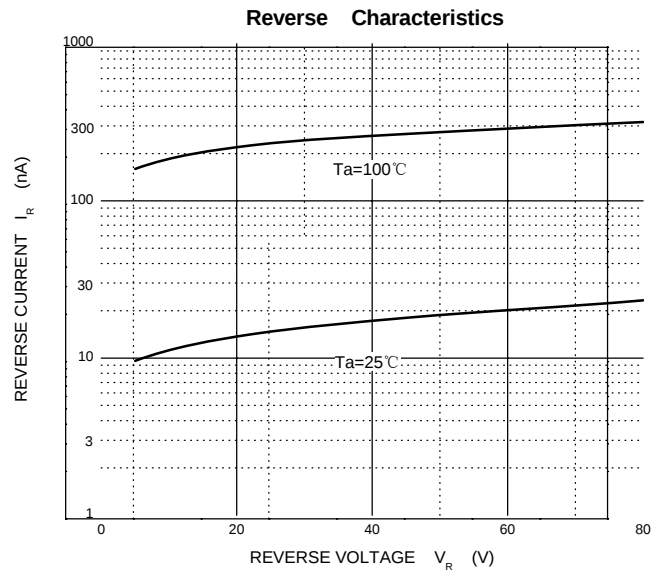
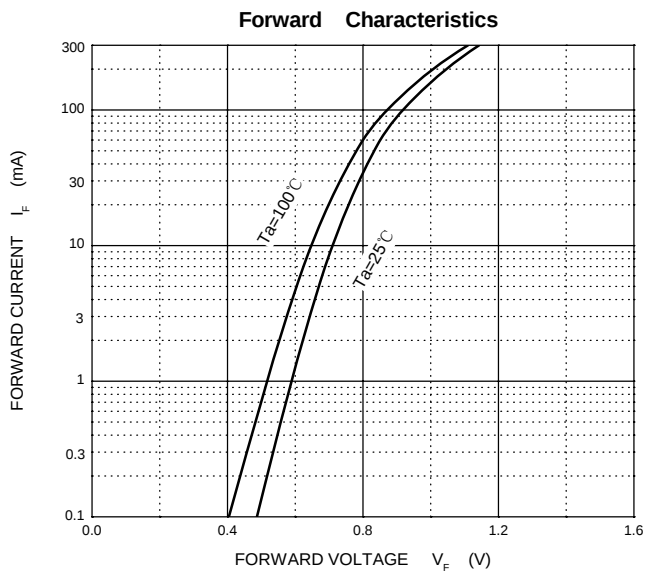
Parameter	Symbol	Min	Typ	Max	Unit	Conditions
Reverse breakdown voltage	V_R	70			V	$I_R=100\mu\text{A}$
Forward voltage	V_{F1}			0.715	V	$I_F=1\text{mA}$
	V_{F2}			0.855	V	$I_F=10\text{mA}$
	V_{F3}			1	V	$I_F=50\text{mA}$
	V_{F4}			1.25	V	$I_F=150\text{mA}$
Reverse current	I_R			2.5	μA	$V_R=70\text{V}$
Capacitance between terminals	C_T			1.5	pF	$V_R=0, f=1\text{MHz}$
Reverse recovery time	t_{rr}			6	ns	$I_F = I_R = 10\text{mA}$, $I_{rr} = 0.1 \times I_R$, $R_L = 100\Omega$



BAW56(A1)BAV70(A4)BAV99(A7)

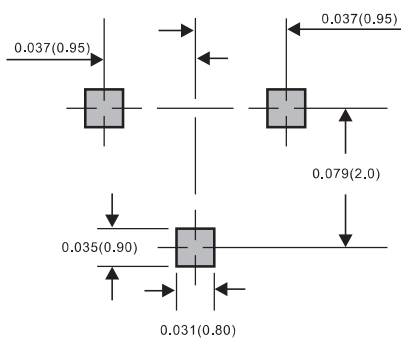
Plastic-Encapsulate Diodes

Typical Characteristics



Suggested solder pad layout

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Dimensions in inches and (millimeters)